

2SD667, 2SD667A

Silicon NPN Epitaxial

REJ03G0769-0200 (Previous ADE-208-1137) Rev.2.00 Aug.10.2005

Application

- Low frequency power amplifier
- Complementary pair with 2SB647/A

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	2SD667	2SD667A	Unit
Collector to base voltage	V _{CBO}	120	120	V
Collector to emitter voltage	V _{CEO}	80	100	V
Emitter to base voltage	V _{EBO}	5	5	V
Collector current	Ic	1	1	Α
Collector peak current	i _{C(peak)}	2	2	A
Collector power dissipation	Pc	0.9	0.9	W
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-50 to +150	°C

Electrical Characteristics

 $(Ta = 25^{\circ}C)$

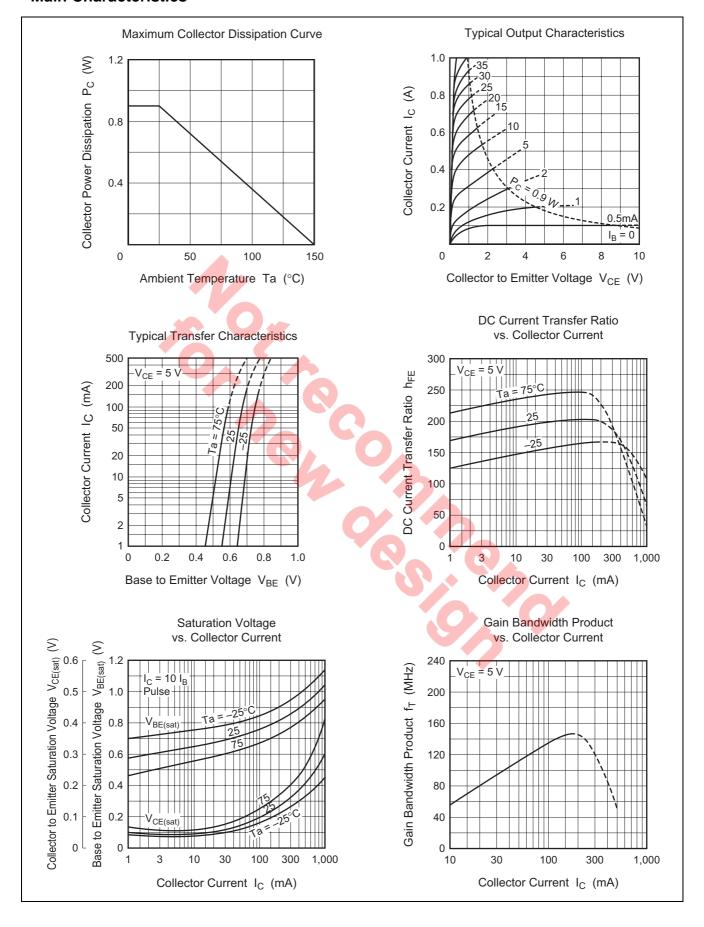
		2SD667			2SD667A				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	120	_	_	120	_	_	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	80	_	_	100	_	_	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	5	_	_	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I _{CBO}	_	_	10	_	_	10	μΑ	$V_{CB} = 100 \text{ V}, I_{E} = 0$
DC current transfer ratio	h _{FE1} *1	60	_	320	60	_	200		$V_{CE} = 5 \text{ V},$ $I_{C} = 150 \text{ mA*}^{2}$
	h _{FE2}	30	_		30	_	_		$V_{CE} = 5 \text{ V},$ $I_{C} = 500 \text{ mA*}^{2}$
Collector to emitter saturation voltage	V _{CE(sat)}	1	_	1	_	_	1	V	$I_C = 500 \text{ mA},$ $I_B = 50 \text{ mA}^{*2}$
Base to emitter voltage	V_{BE}	1	_	1.5	_	_	1.5	V	$V_{CE} = 5 \text{ V},$ $I_{C} = 150 \text{ mA*}^{2}$
Gain bandwidth product	fτ		140		_	140	_	MHz	$V_{CE} = 5 \text{ V},$ $I_{C} = 150 \text{ mA*}^{2}$
Collector output capacitance	Cob	_	12	_	_	12	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 1 MHz

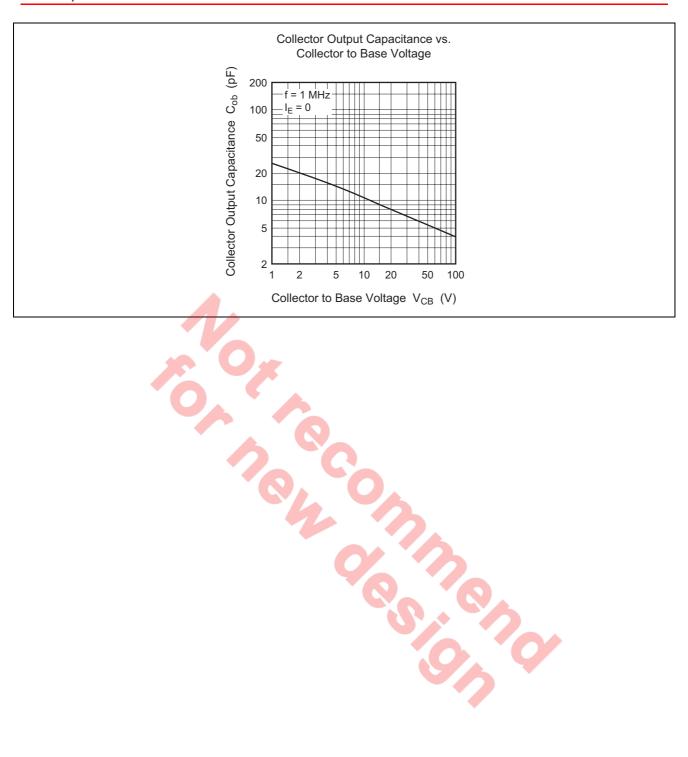
Notes: 1. The 2SD667 and 2SD667A are grouped by h_{FE1} as follows.

2. Pulse test

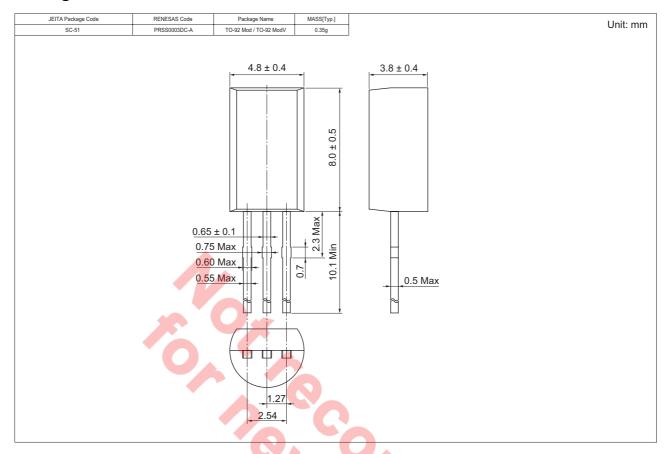
Notes: 1. TI	ne 2SD667 and	I 2SD667A are	grouped by hee	as follows.	
2. P	ulse test				
	В	С	D		
2SD667	60 to 120	100 to 200	160 to 320		
2SD667A	60 to 120	100 to 200			
				~ ~	
				10 10	
					0/

Main Characteristics





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SD667BTZ-E	2500	Hold Box, Radial Taping
2SD667CTZ-E		
2SD667DTZ-E		
2SD667ABTZ-E		
2SD667ACTZ-E		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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